

LVDS SERDES TRANSMITTER

FEATURES

- 28:4 Data Channel Compression at up to 1.904 Gigabits per Second Throughput
- Suited for Point-to-Point Subsystem Communication With Very Low EMI
- 28 Data Channels Plus Clock in Low-Voltage TTL and 4 Data Channels Plus Clock Out Low-Voltage Differential
- Selectable Rising or Falling Clock Edge Triggered Inputs
- Bus Pins Tolerate 6-kV HBM ESD
- Operates From a Single 3.3-V Supply and 250 mW (Typ)
- 5-V Tolerant Data Inputs
- Packaged in Thin Shrink Small-Outline Package With 20 Mil Terminal Pitch
- Consumes <1 mW When Disabled
- Wide Phase-Lock Input Frequency Range 20 MHz to 68 MHz
- No External Components Required for PLL
- Outputs Meet or Exceed the Requirements of ANSI EIA/TIA-644 Standard
- Industrial Temperature Qualified T_A = -40°C to 85°C
- Replacement for the DS90CR285

DESCRIPTION

The SN65LVDS93 LVDS serdes (serializer/deserializer) transmitter contains four 7-bit parallel-load serial-out shift registers, a 7xclock synthesizer, and five low-voltage differential signaling (LVDS) drivers in a single integrated circuit. These functions allow 28 bits of single-ended LVTTL data to be synchronously transmitted over five balanced-pair conductors for receipt by a compatible receiver, such as the SN65LVDS94.

When transmitting, data bits D0 through D27 are each loaded into registers upon the edge of the input clock signal (CLKIN). The rising or falling edge of the clock can be selected via the clock select (CLKSEL) pin. The frequency of CLKIN is multiplied seven times and then used to serially unload the data registers in 7-bit slices. The four serial streams and a phase-locked clock (CLKOUT) are then output to LVDS output drivers. The frequency of CLKOUT is the same as the input clock, CLKIN.

DGG PACKAGE (TOP VIEW)

		_	1
V _{cc} [1 •	56] D4
D5 [2	55] D3
D6 [3	54] D2
D7 [4	53] GND
GND [5	52] D1
D8 [6	51] D0
D9 [7	50	D27
D10 [8	49	LVDSGND
V _{CC} [9	48] Y1M
D11 [10	47] Y1P
D12 [11	46] Y2M
D13 [12	45] Y2P
GND [13	44	LVDSV _{CC}
D14 [14	43	LVDSGND
D15 [15	42] Y3M
D16 [16	41] Y3P
CLKSEL [17	40] CLKOUTM
D17 [18	39] CLKOUTP
D18 [19	38] Y4M
D19 [20	37] Y4P
GND [21	36	LVDSGND
D20 [22	35] PLLGND
D21 [23	34] PLLV _{CC}
D22 [24	33] PLLGND
D23 [25	32	SHTDN
V _{CC} [26	31	CLKIN
D24 [27	30	D26
D25 [28	29] GND



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





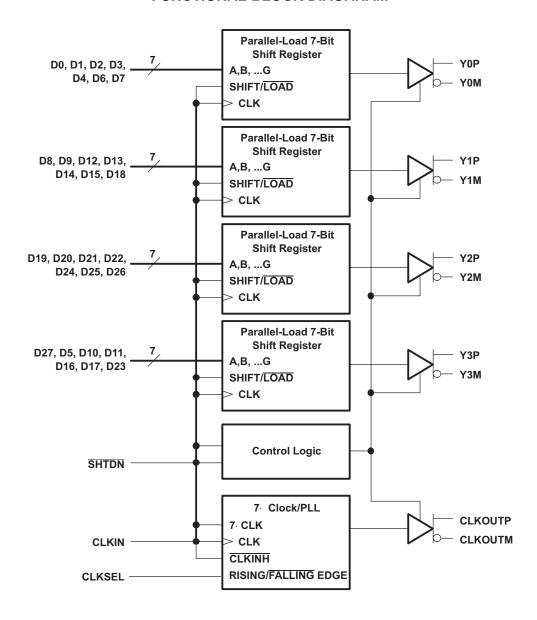
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DESCRIPTION (CONTINUED)

The SN65LVDS93 requires no external components and little or no control. The data bus appears the same at the input to the transmitter and output of the receiver with the data transmission transparent to the user(s). The only user intervention is selecting a clock rising edge by inputting a high level to CLKSEL or a falling edge with a low-level input and the possible use of the shutdown/clear (SHTDN). SHTDN is an active-low input to inhibit the clock and shut off the LVDS output drivers for lower power consumption. A low level on this signal clears all internal registers at a low level.

The SN65LVDS93 is characterized for operation over ambient air temperatures of -40°C to 85°C.

FUNCTIONAL BLOCK DIAGARAM



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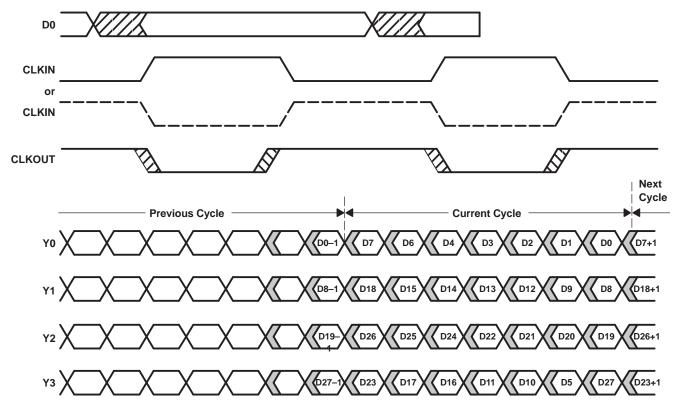
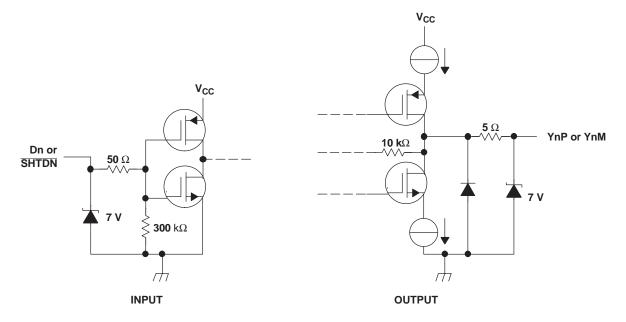


Figure 1. Typical 'LVDS93 Load and Shift Sequences

EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS





ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)(1)

			UNIT
V_{CC}	Supply voltage range (2)		−0.5 V to 4 V
Vo	Voltage range at any output te	-0.5 V to V _{CC} + 0.5 V	
V_{I}	Voltage range at any input terr	ninal	-0.5 V to 5.5 V
		Bus Pins (Class 3A)	6 KV
	Electrostatic discharge ⁽³⁾	Bus Pins (Class 2B)	400 V
	Electrostatic discharge	Bus Pins (Class 2A)	6 KV
		Bus Pins (Class 2B)	200 V
	Continuous total power dissipa	tion	See Dissipation Rating Table
T _A	Operating free-air temperature	range	-40°C to 85°C
T _{stg}	Storage temperature range		-65°C to 150°C
	Lead temperature 1,6 mm (1/1	6 inch) from case for 10 seconds	260°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C	DERATING FACTOR ⁽¹⁾	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C	POWER RATING	POWER RATING
DGG	1377 mW	11 mW/°C	882 mW	717 mW

⁽¹⁾ This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	3	3.3	3.6	٧
V_{IH}	High-level input voltage	2			V
V_{IL}	Low-level input voltage			0.8	V
Z_{L}	Differential load impedance	90		132	Ω
T_A	Operating free-air temperature	-40		85	°C

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⁽²⁾ All voltage values are with respect to the GND terminals.

⁽³⁾ This rating is measured using MIL-STD-883C Method, 3015.7.



ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _T	Input voltage threshold			1.4		V
V _{OD}	Differential steady-state output voltage magnitude		247		454	mV
Δ V _{OD}	Change in the steady-state differential output voltage magnitude between opposite binary states	$R_L = 100 \Omega$, See Figure 3			50	mV
V _{OC(SS)}	Steady-state common-mode output voltage	See Figure 3	1.125		1.375	V
V _{OC(PP)}	Peak-to-peak common-mode output voltage				150	mV
I _{IH}	High-level input current	V _{IH} = V _{CC}			20	μΑ
I _{IL}	Low-level input current	V _{IL} = 0 V			±10	μΑ
	Chart circuit output ourrent	V _{OY} = 0 V			±24	mA
Ios	Short-circuit output current	V _{OD} = 0 V			±12	mA
l _{OZ}	High-impedance state output current	$V_{O} = 0 \text{ V to } V_{CC}$			±20	μΑ
		Disabled, All inputs at GND			350	μΑ
I _{CC(AVG)}	Quiescent current (average)	Enabled, R_L = 100 Ω (5 places), Worst-case pattern (see Figure 4), t_c = 15.38 ns		95	120	mA
Ci	Input capacitance			3		pF

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

TIMING REQUIREMENTS

		MIN	NOM	MAX	UNIT
t _c	Input clock period	14.7	t _c	50	ns
t_w	High-level input clock pulse width duration	0.4t _c		0.6t _c	ns
t _t	Input signal transition time			5	ns
t_{su}	Data setup time, D0 through D27 before CLKIN↑ or CLKIN↓ (see Figure 2)	3			ns
t _h	Data hold time, D0 through D27 after CLKIN↓ or CLKIN↑ (see Figure 2)	1.5			ns

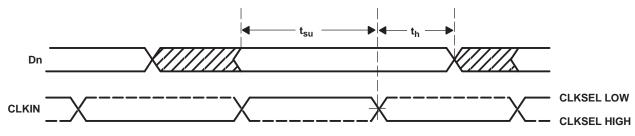


SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t ₀	Delay time, CLKOUT↑ to serial bit position 0		-0.20	0	0.20	ns
t ₁	Delay time, CLKOUT↑ to serial bit position 1		$\frac{1}{7}t_{C} - 0.20$		$\frac{1}{7}$ t _C + 0.20	ns
t ₂	Delay time, CLKOUT↑ serial bit position 2		$\frac{2}{7}t_{\rm C} - 0.20$		$\frac{2}{7}t_{C} + 0.20$	ns
t ₃	Delay time, CLKOUT↑ serial bit position 3	$t_c = 15.38 \text{ ns } (\pm 0.2\%),$	$\frac{3}{7}t_{C}-0.20$		$\frac{3}{7}t_{\rm C} + 0.20$	ns
t ₄	Delay time, CLKOUT↑ to serial bit position 4	Input clock jitter < 50 ps ⁽²⁾ , See Figure 5	$\frac{4}{7}t_{C}-0.20$		$\frac{4}{7}t_{C} + 0.20$	ns
t ₅	Delay time, CLKOUT↑ to serial bit position 5		$\frac{5}{7}t_{C} - 0.20$		$\frac{5}{7}$ t _C + 0.20	ns
t ₆	Delay time, CLKOUT↑ to serial bit position 6		$\frac{6}{7}t_{C}-0.20$		$\frac{6}{7}t_{C} + 0.20$	ns
t _{sk(o)}	Output skew, $t_n - \frac{n}{7}t_c$		-0.20		0.20	ns
t ₇	Delay time, CLKIN↓ or CLKIN↑ to CLKOUT↑	t_c = 15.38 ns (±0.2%), Input clock jitter < 50 ps ⁽²⁾ , See Figure 5		4.2		ns
t _{c(o)}	Output clock period			t _c		ps
۸٠	Output clock cycle-to-cycle jitter ⁽³⁾	t_c = 15.38 ns + 0.75sin (2 π 500E3t) ± 0.05 ns, See Figure 6		±80		ps
Δt _{c(o)}	Output clock cycle-to-cycle juter 147	t_c = 15.38 ns + 0.75sin (2 π 3E6t) ± 0.05 ns, See Figure 6		±300		ns
t _w	High-level output clock pulse duration			$\frac{4}{7}t_{C}$		ps
t _t	Differential output voltage transition time (t _r or t _f)	See Figure 3	260	700	1500	ps
t _{en}	Enable time, SHTDN↑ to phase lock (Yn valid)	See Figure 7		1		ms
t _{dis}	Disable time, SHTDN↓ to off-state (CLKOUT low)	See Figure 8		250		ns

PARAMETER MEASUREMENT INFORMATION



All input timing is defined at 1.4 V on an input signal with a 10% to 90% rise or fall time of less than 5 ns. note:

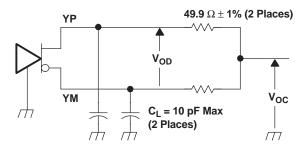
Figure 2. Setup and Hold Time Definition

All typical values are at V_{CC} = 3.3 V, T_A = 25°C. Input clock jitter is the magnitude of the charge in the input clock period

The output clock jitter is the change in the output clock period from one cycle to the next cycle observed over 15,000 cycles.



PARAMETER MEASUREMENT INFORMATION (continued)



NOTE A: The lumped instrumentation capacitance for any single-ended voltage measurement is less than or equal to 10 pF. When making measurements at YP or YM, the complementary output is similarly loaded.

(a) SCHEMATIC

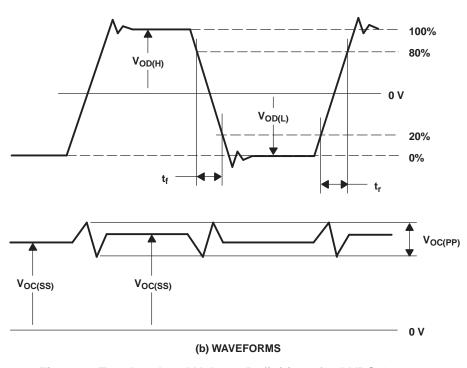
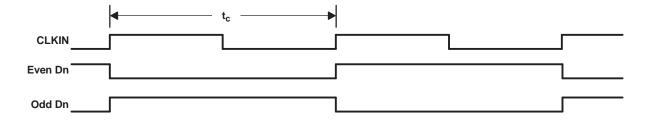


Figure 3. Test Load and Voltage Definitions for LVDS Outputs



NOTE A: The worst-case test pattern produces nearly the maximum switching frequency for all of the LVDS outputs. Pattern with CLKSEL low shown.

Figure 4. Worst-Case Test Pattern (CLKSEL Low Shown)



PARAMETER MEASUREMENT INFORMATION (continued)

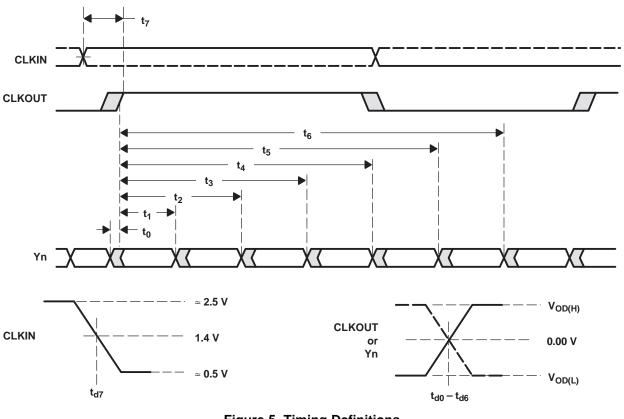
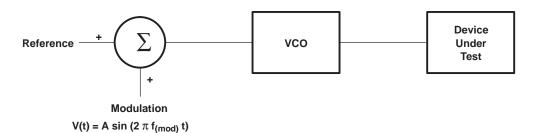


Figure 5. Timing Definitions



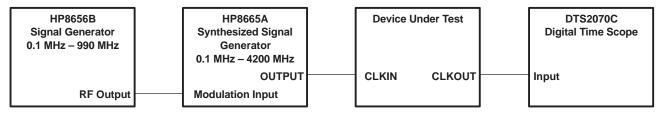


Figure 6. Output Clock Jitter Test Setup



PARAMETER MEASUREMENT INFORMATION (continued)

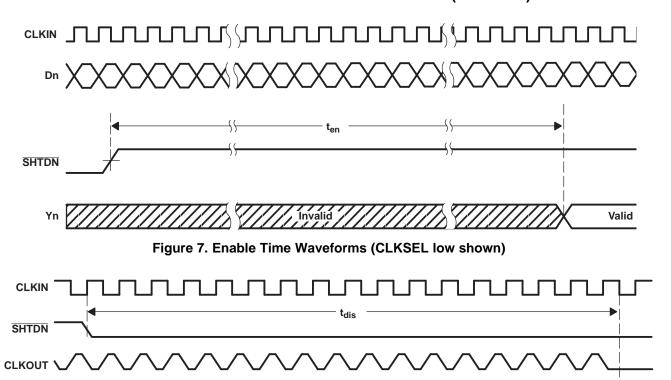


Figure 8. Disable Time Waveforms (CLKSEL low shown)

TYPICAL CHARACTERISTICS

WORST-CASE SUPPLY CURRENT FREQUENCY 120 $V_{CC} = 3.6 \text{ V}$ 100 ICC - Supply Current - mA 80 $V_{CC} = 3 V$ 60 $V_{CC} = 3.3 V$ 40 20 0 30 40 50 60 70 f - Frequency - MHz

Figure 9.



APPLICATION INFORMATION

16-BIT BUS EXTENSION

In a 16-bit bus application (Figure 10), TTL data and clock coming from bus transceivers that interface the backplane bus arrive at the Tx parallel inputs of the LVDS serdes transmitter. The clock associated with the bus is also connected to the device. The on-chip PLL synchronizes this clock with the parallel data at the input. The data is then multiplexed into three different line drivers which perform the TTL to LVDS conversion. The clock is also converted to LVDS and presented to a separate driver. This synchronized LVDS data and clock at the receiver, which recovers the LVDS data and clock, performs a conversion back to TTL. Data is then demultiplexed into a parallel format. An on-chip PLL synchronizes the received clock with the parallel data, and then all are presented to the parallel output port of the receiver.

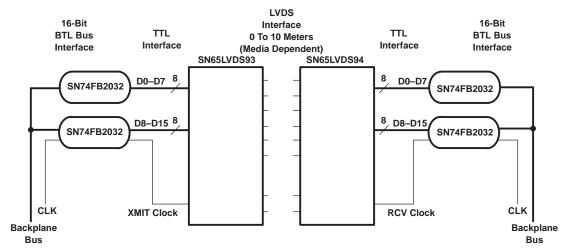


Figure 10. 16-Bit Bus Extension

16-BIT BUS EXTENSION WITH PARITY

In the previous application we did not have a checking bit that would provide assurance that the data crosses the link. If we add a parity bit to the previous example, we would have a diagram similar to the one in Figure 11. The device following the SN74FB2032 is a low-cost parity generator. Each transmit-side transceiver/parity generator takes the LVTTL data from the corresponding transceiver, performs a parity calculation over the byte, and then passes the bits with its calculated parity value on the parallel input of the LVDS serdes transmitter. Again, the on-chip PLL synchronizes this transmit clock with the eighteen parallel bits (16 data + 2 parity) at the input. The synchronized LVDS data/parity and clock arrive at the receiver.

The receiver performs the conversion from LVDS to LVTTL and the transceiver/parity generator performs the parity calculations. These devices compare their corresponding input bytes with the value received on the parity bit. The transceiver/parity generator will assert its parity error output if a mismatch is detected.

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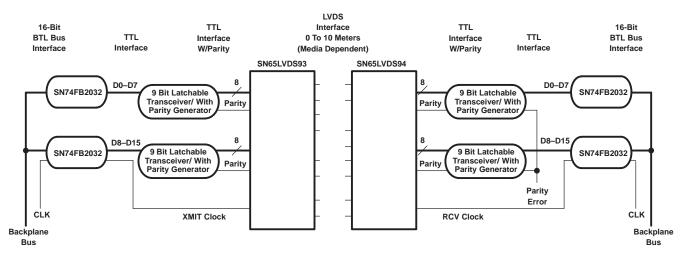


Figure 11. 16-Bit Bus Extension With Parity

low cost virtual backplane transceiver

Figure 12 represents LVDS serdes in an application as a virtual backplane transceiver (VBT). The concept of a VBT can be achieved by implementing individual LVDS serdes chipsets in both directions of subsystem serialized links.

Depending on the application, the designer will face varying choices when implementing a VBT. In addition to the devices shown in Figure 12, functions such as parity and delay lines for control signals could be included. Using additional circuitry, half-duplex or full-duplex operation can be achieved by configuring the clock and control lines properly.

The designer may choose to implement an independent clock oscillator at each end of the link and then use a PLL to synchronize LVDS serdes's parallel I/O to the backplane bus. Resynchronizing FIFOs may also be required.

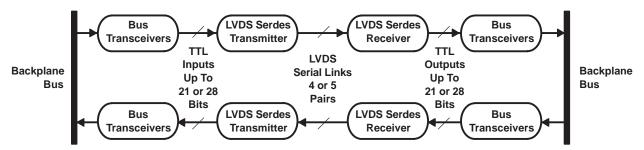


Figure 12. Virtual Backplane Transceiver



PACKAGE OPTION ADDENDUM



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65LVDS93DGG	ACTIVE	TSSOP	DGG	56	35	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR		SN65LVDS93	Samples
SN65LVDS93DGGG4	ACTIVE	TSSOP	DGG	56	35	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR		SN65LVDS93	Samples
SN65LVDS93DGGR	ACTIVE	TSSOP	DGG	56	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SN65LVDS93	Samples
SN65LVDS93DGGRG4	ACTIVE	TSSOP	DGG	56	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SN65LVDS93	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDS93DGGR	TSSOP	DGG	56	2000	330.0	24.4	8.6	15.6	1.8	12.0	24.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS93DGGR	TSSOP	DGG	56	2000	350.0	350.0	43.0



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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